

M5M27400AK-10,-12,-15

4194304-BIT(524288-WORD BY 8-BIT/262144-WORD BY 16-BIT)
CMOS ERASABLE AND ELECTRICALLY REPROGRAMMABLE ROM

DESCRIPTION

The Mitsubishi M5M27400AK is a high-speed 4194304-bit ultraviolet erasable and electrically reprogrammable read only memory. It is suitable for microprocessor programming applications where rapid turn-around is required. The M5M27400AK is fabricated by N-channel double polysilicon gate for Memory and CMOS technology for peripheral circuits, and is available in a 40-pin DIP with a transparent lid.

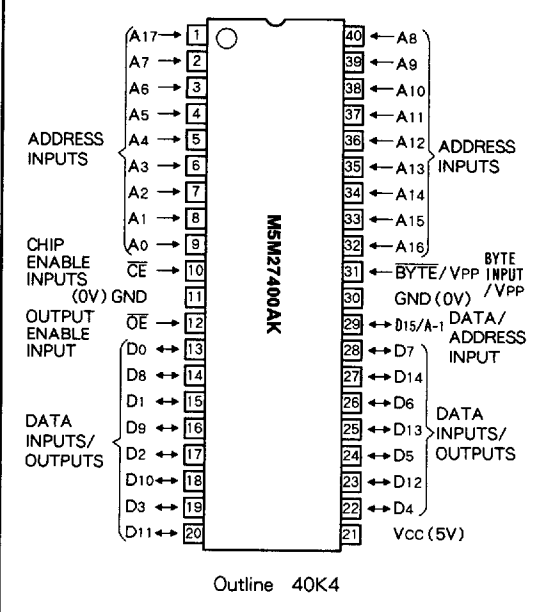
FEATURES

- 524288-word × 8-bit/262144-word × 16-bit organization
- Access time M5M27400AK-10 100ns (max.)
M5M27400AK-12 120ns (max.)
M5M27400AK-15 150ns (max.)
- Single 5V power supply (read operation)
- Programming Voltage 12.75V
- Input and output TTL-compatible in read and program mode
- Standard 40-pin DIP
- Word programming algorithm

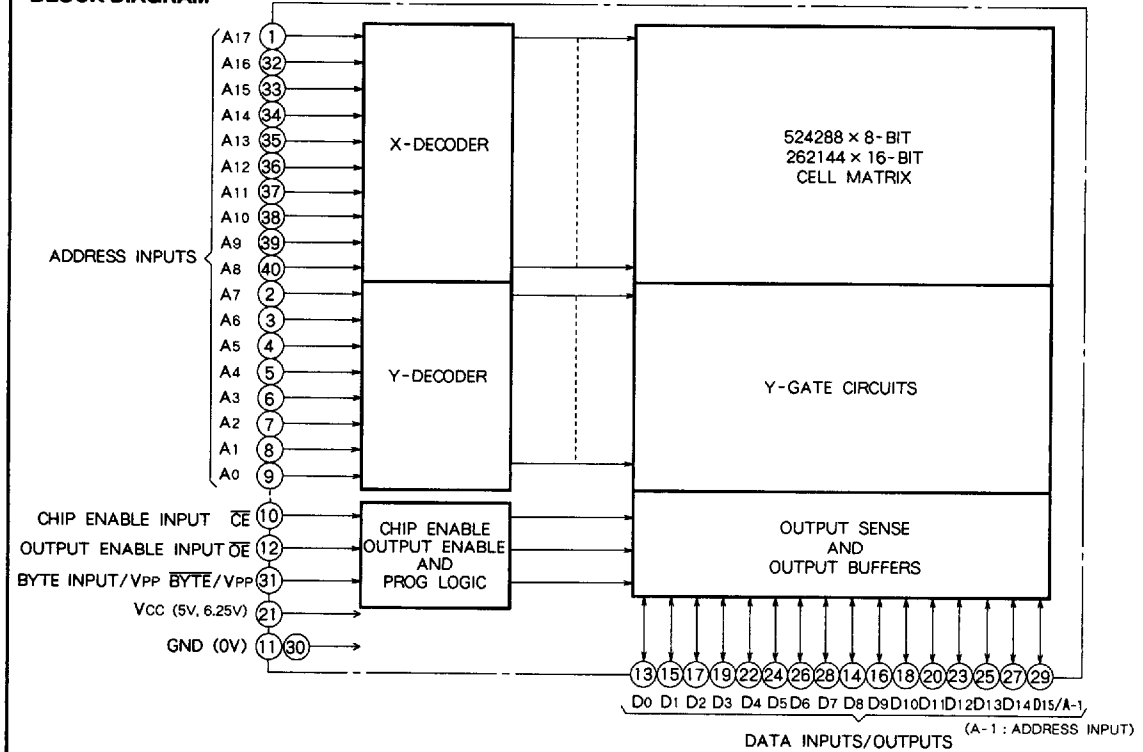
APPLICATION

Microcomputer systems and peripheral equipment

PIN CONFIGURATION (TOP VIEW)



BLOCK DIAGRAM



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FUNCTION

Read

Read mode is initiated by \overline{CE} and \overline{OE} low. High level input to \overline{BYTE} and address signals to the address inputs ($A_0 \sim A_{17}$) make the data contents of the designated address location available at the data outputs ($D_0 \sim D_{15}$).

When the \overline{BYTE} signal is low, address inputs are $A-1, A_0 \sim A_{17}$ and data outputs are $D_0 \sim D_7$.

When the \overline{CE} or \overline{OE} signal is high, data outputs are in a floating state.

When the \overline{CE} signal is high, the device is in the stand by mode or power-down mode.

Programming

(Word programming algorithm)

The M5M27400AK enters the word programming mode when 12.75V is supplied to the \overline{BYTE}/V_{PP} power supply input and

\overline{OE} is at high level. A location is designated by address signals ($A_0 \sim A_{17}$), and the data to be programmed must be applied at 8-bits in parallel to the data inputs ($D_0 \sim D_{15}$). In this state, word programming is completed when \overline{CE} is at low level.

Erase

Erase is effected by exposure to ultraviolet light with a wavelength of 2537 Å at an intensity of approximately 15WS/cm². Sunlight and fluorescent light may contain ultraviolet light sufficient to erase the programmed information. For any operation in the read mode, the transparent lid should be covered with opaque tape.

MODE SELECTION

Mode \ Pins	\overline{CE}	\overline{OE}	\overline{BYTE}/V_{PP}	V_{CC}	Data I/O $D_0 \sim 7$	Data I/O $D_8 \sim 14$	Data I/O $D_{15}/A-1$
Read (Word mode)	V _{IL}	V _{IL}	V _{IH}	5V	Data out	Data out	Data out
Read (Byte mode)	V _{IL}	V _{IL}	V _{IL}	5V	Data out	Floating	A-1 input
Output disable	V _{IL}	V _{IH}	X*	5V	Floating	Floating	Floating
Standby (Power down)	V _{IH}	X*	X*	5V	Floating	Floating	Floating
Programming	V _{IL}	V _{IH}	12.75V	6.25V	Data in	Data in	Data in
Program verify	V _{IH}	V _{IL}	12.75V	6.25V	Data out	Data out	Data out
Program inhibit	V _{IH}	V _{IH}	12.75V	6.25V	Floating	Floating	Floating

* : X can be either V_{IL} or V_{IH}

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Conditions	Ratings	Unit
V _{I1}	All input to output voltage except $\overline{BYTE}/V_{PP} \cdot A_9$	With respect to Ground	- 0.6~7	V
V _{I2}	\overline{BYTE}/V_{PP} supply voltage		- 0.6~14.0	V
V _{I3}	A_9 supply voltage		- 0.6~13.5	V
T _{opr}	Operating temperature		- 10~80	°C
T _{stg}	Storage temperature		- 65~125	°C

Note 1: Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or at any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods affects device reliability.

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READ OPERATION

DC ELECTRICAL CHARACTERISTICS (Ta = 0~70°C, Vcc = 5V ± 10%, unless otherwise noted)

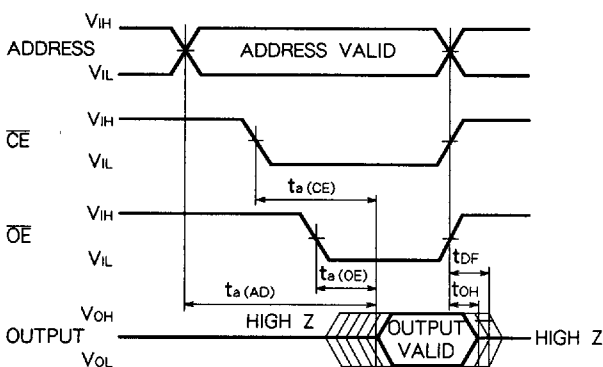
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ILI	Input leakage current	V _{IN} = 0~V _{CC}			10	μA
ILO	Output leakage current	V _{OUT} = 0~V _{CC}			10	μA
I _{PP1}	V _{PP} current read/stand-by	V _{PP} = V _{CC} = 5.5V		1	100	μA
I _{SB1}	V _{CC} current stand-by	$\overline{CE} = V_{IH}$			1	mA
I _{SB2}		$\overline{CE} = V_{CC}$		1	100	μA
I _{CC1}	V _{CC} current active	$\overline{CE} = \overline{OE} = V_{IL}$, DC, I _{OUT} = 0mA			50	mA
I _{CC2}		$\overline{CE} = V_{IL}$, f = 10MHz, I _{OUT} = 0mA			70	mA
V _{IL}	Input low voltage		-0.1		0.8	V
V _{IH}	Input high voltage		2.2		V _{CC} +1	V
V _{OL}	Output low voltage	I _{OL} = 2.1mA			0.45	V
V _{OH}	Output high voltage	I _{OH} = -400 μA	2.4			V

Note 2: Typical values are at Ta = 25°C and nominal supply voltages.

AC ELECTRICAL CHARACTERISTICS (Ta = 0~70°C, Vcc = 5V ± 10%, unless otherwise noted)

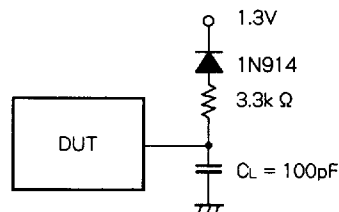
Symbol	Parameter	Test conditions	Limits						Unit
			M5M27400AK-10		M5M27400AK-12		M5M27400AK-15		
			Min.	Max.	Min.	Max.	Min.	Max.	
t _{a(AD)}	Address to output delay	$\overline{CE} = \overline{OE} = V_{IL}$		100		120		150	ns
t _{a(CE)}	\overline{CE} to output delay	$\overline{OE} = V_{IL}$		100		120		150	ns
t _{a(OE)}	\overline{OE} to output delay	$\overline{CE} = V_{IL}$		50		60		60	ns
t _{DF}	\overline{OE} high to output float	$\overline{CE} = V_{IL}$	0	45	0	50	0	50	ns
t _{OH}	Output hold from \overline{CE} , \overline{OE} or address		0		0		0		ns

AC WAVEFORMS



Test conditions for A.C. characteristics
 Input voltage: V_{IL} = 0.45V, V_{IH} = 2.4V
 Input rise and fall times: ≤ 10ns
 Reference voltage at timing measurement: 1.5V

Output load: 1 TTL gate + C_L (= 100pF)
 or



CAPACITANCE

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
C _{IN}	Input capacitance (Address, \overline{CE} , \overline{OE})	Ta = 25°C, f = 1MHz, V _I = V _O = 0V			15	pF
C _{OUT}	Output capacitance				15	pF

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PROGRAM OPERATION

First set $V_{CC} = 6.25V$, $\overline{BYTE}/V_{PP} = 12.75V$ and then set an address to first address to be programmed. After applying 0.1ms program pulse (\overline{CE}) to the address, verify is performed. If the output data of that address is not verified correctly, apply one more 0.1ms program pulse. The programmer continues 0.1ms pulse-then-verify routines until the device verify correctly or twenty five of these pulse-then-verify routines

have been completed. When the programming procedure above is finished, step to the next address and repeat this procedure till last address to be programmed. When the entire addresses have been programmed completely, all addresses should be verified with $V_{CC} = \overline{BYTE}/V_{PP} = 5V$.

DC ELECTRICAL CHARACTERISTICS ($T_a=25 \pm 5^\circ C$, $V_{CC}=6.25V \pm 0.25V$, $\overline{BYTE}/V_{PP}=12.75V \pm 0.25V$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{LI}	Input leakage current	$V_{IN} = 0 \sim V_{CC}$			10	μA
V_{OL}	Output low voltage (verify)	$I_{OL} = 2.1mA$			0.45	V
V_{OH}	Output high voltage (verify)	$I_{OH} = -400 \mu A$	2.4			V
V_{IL}	Input low voltage		-0.1		0.8	V
V_{IH}	Input high voltage		2.2		V_{CC}	V
I_{CC}	V_{CC} supply current				30	mA
I_{PP}	V_{PP} supply current	$\overline{CE} = V_{IL}$			50	mA

AC ELECTRICAL CHARACTERISTICS ($T_a=25 \pm 5^\circ C$, $V_{CC}=6.25V \pm 0.25V$, $\overline{BYTE}/V_{PP}=12.75V \pm 0.25V$, unless otherwise noted)

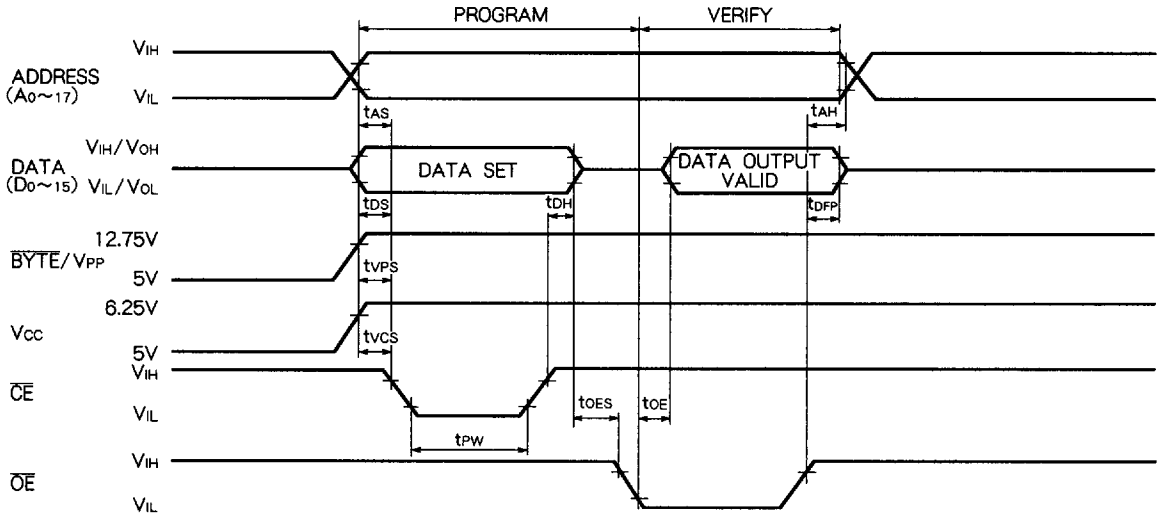
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
t_{AS}	Address setup time		2			μs
t_{OES}	\overline{OE} setup time		2			μs
t_{DS}	Data setup time		2			μs
t_{AH}	Address hold time		0			μs
t_{DH}	Data hold time		2			μs
t_{DFP}	Chip enable to output float delay		0		130	ns
t_{VCS}	V_{CC} setup time		2			μs
t_{VPS}	\overline{BYTE}/V_{PP} setup time		2			μs
t_{PW}	\overline{CE} initial program pulse width		95	100	105	μs
t_{OE}	Data valid from \overline{OE}				150	ns

Note 3: V_{CC} must be applied simultaneously \overline{BYTE}/V_{PP} and removed simultaneously \overline{BYTE}/V_{PP} .

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AC WAVEFORMS



Test conditions for A.C. characteristics

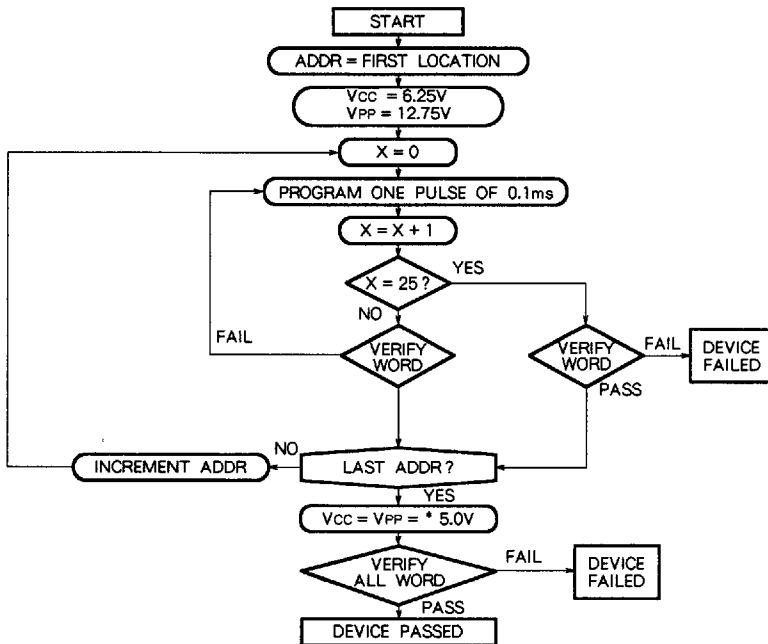
Input voltage : $V_{IL} = 0.45V$, $V_{IH} = 2.4V$

Input rise and fall times : $\leq 20ns$

Reference voltage at timing measurement : Input, Output

"L" = 0.8V, "H" = 2V.

PROGRAMMING ALGORITHM FLOW CHART



* $4.5V \leq V_{CC} = V_{PP} \leq 5.5V$

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DEVICE IDENTIFIER MODE

The Device Identifier Mode allows the reading of a binary code from the EPROM that identifier the manufacturer and device type.

The EPROM Programmer reads the manufacturer code and the device code and automatically selects the corresponding programming algorithm.

M5M27400AK DEVICE IDENTIFIER CODE

Code \ Pin	A ₀	D ₁₅	D ₁₄	D ₁₃	D ₁₂	D ₁₁	D ₁₀	D ₉	D ₈	D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀	Hex Data
Manufacturer code	V _{IL}	0	0	0	0	0	0	0	0	0	0	0	1	1	1	0	0	001C
Device code	V _{IH}	0	0	0	0	0	0	0	0	1	0	0	1	0	0	0	1	0091

Note 5: A₉ = 12.0V ± 0.5V
 A₁~A₈, A₁₀~A₁₇, \overline{CE} , \overline{OE} = V_{IL}, BYTE/V_{PP} = V_{IH}
 V_{CC} = 5V ± 10%

